PRODUCT INFORMATION

SHARP

LH53BV64R00N 64M MROM

FEATURES

- Memory organization
 - 4,194,304 × 16-bit (Word mode: $\overline{W} = V_{IL}$)
 - 2,097,152 × 32-bit (Double word mode: $\overline{W} = V_{IH}$)
- Supply voltage 3.3 V to ± 0.3 V •
- Static operation ٠
- Three-state output
- Access time 120 ns (MAX.), 50 ns (MAX.) in page mode •
- Addressable page: 4 double words or 8 words •
- 70-pin SSOP ٠
- Operating current 120 mA (MAX.) •
- Standby current 150 µA (MAX.)
- Not programmable •
- Not designed or rated as radiation hardened •
- CMOS process (P-type silicon substrate)

DESCRIPTION

The SHARP LH53BV64R00N is a 64M CMOS mask ROM (maskprogrammable read-only memory), producted by the silicon gate CMOS process.

PIN DESCRIPTION

PIN	DESCRIPTION
A_{-1} to A_1	Address Input (Page Mode Operation)
A_2 to A_{20}	Address Input
D ₀ to D ₃₁	Data Output
W	\times 16-bit/ \times 32bit Mode Select Input*
CE	Chip Enable Input*
ŌĒ	Output Enable Input*
V _{CC}	Power Pin (+3.3 V)
GND	Ground
NC	Non Connection

NOTE: D_{31}/A_1 pin becomes LSB address input (A₁) when the \overline{W} pin is set to be low in word mode, and data output (D₃₁) when set to be high in double word mode. **APPLICATIONS:**

PDA Printer

Integrated Circuits Group

70-PIN SSOP PINOUT



NOTE: The D₃₁/A₋₁ pin becomes LSB address input (A₋₁) when the \overline{W} pin is set to LOW in word mode, and data output (D₃₁) when set to HIGH in double word mode. 64R00-1

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